# **NPN EPITAXIAL** TIP140/141/142

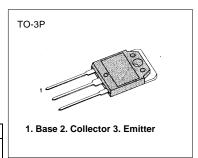
# SILICON DARLINGTON TRANSISTOR

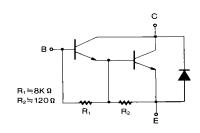
**HIGH DC CURRENT GAIN** MIN  $h_{FE} = 1000$  @  $V_{CE} = 4V$ , IC = 5AMONOLITHIC CONSTRUCTION WITH BUILT IN BASE-EMITTER SHUNT RESISTORS **INDUSTRIAL USE** 

• Complement to TIP145/146/147

# **ABSOLUTE MAXIMUM RATINGS**

Characteristic	Symbol	Rating	Unit
Collector Base Voltage	$V_{CBO}$		
: TIP140		60	V
: TIP141		80	V
: TIP142		100	V
Collector Emitter Voltage	$V_{CEO}$		
: TIP140		60	V
: TIP141		80	V
: TIP142		100	V
Emitter-Base Voltage	V <sub>EBO</sub>	5	V
Collector Current (DC)	Ic	10	Α
Collector Current (Pulse)	Ic	15	Α
Base Current (DC)	I <sub>B</sub>	0.5	Α
Collector Dissipation (T <sub>C</sub> =25°C)	Pc	125	W
Junction Temperature	TJ	150	°C
Storage Temperature	T <sub>STG</sub>	- 65 ~ 150	°C

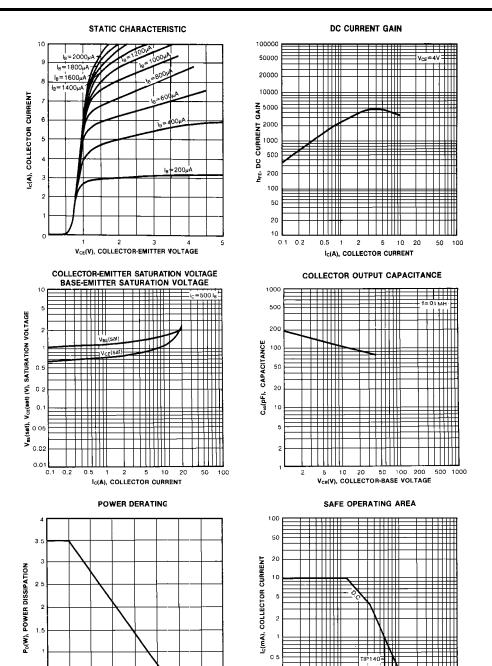




# **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> =25°C)

Characteristic	Symbol	Test Conditions	Min	Тур	Max	Unit
Collector Emitter Sustaining Voltage	V <sub>CEO</sub> (sus)					
: TIP140F		$I_C = 30 \text{mA}, I_B = 0$	60			V
: TIP141F			80			V
: TIP142F			100			V
Collector Cutoff Current : TIP140F	I <sub>CEO</sub>	$V_{CE} = 30V, I_{B} = 0$			2	mA
: TIP141F		$V_{CE} = 40V, I_B = 0$			2	mA
: TIP142F		$V_{CE} = 50V, I_B = 0$			2	mA
Collector Cutoff Current : TIP140F	I <sub>CBO</sub>	$V_{CB} = 60V, I_E = 0$			1	mA
: TIP141F		$V_{CB} = 80V, I_{E} = 0$			1	mA
: TIP142F		$V_{CB} = 100V, I_{E} = 0$			1	mA
Emitter Cutoff Current	I <sub>EBO</sub>	$V_{BE} = 5V, I_{C} = 0$			2	mA
DC Current Gain	h <sub>FE</sub>	$V_{CE} = 4V$ , $I_C = 5A$	1000			
		$V_{CE} = 4V, I_{C} = 10A$	500			
Collector Emitter Saturation Voltage	V <sub>CE</sub> (sat)	$I_C = 5A, I_B = 10mA$			2	V
		$I_C = 10A, I_B = 40mA$			3	V
Base Emitter Saturation Voltage	V <sub>BE</sub> (sat)	$I_C = 10A$ , $I_B = 40mA$			3.5	V
Base Emitter On Voltage	V <sub>BE</sub> (on)	$V_{CE} = 4V, I_{C} = 10A$			3	V
Delay Time	t <sub>D</sub>	$V_{CC} = 30V, I_{C} = 5A$		0.15		μs
Rise Time	t <sub>R</sub>	$I_B = 20 \text{mA}, I_{B1} = -I_{B2}$		0.55		μs
Storage Time	t <sub>STG</sub>			2.5		μs
Fall Time	t <sub>F</sub>			2.5		μs





02

175 200

5 10 20 50 100 200 500 V<sub>CE</sub>(V), COLLECTOR-EMITTER VOLTAGE



75

100 125

Tc(°C), CASE TEMPERATURE

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